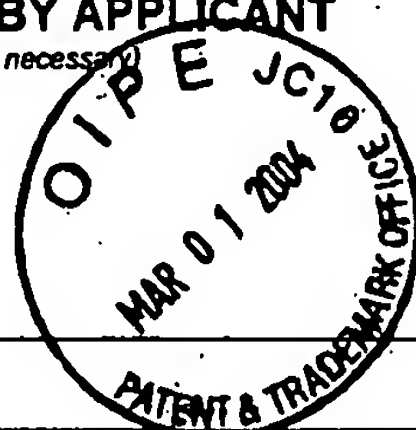


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|----------------------|---------------------|
| Application Number | 10/612793 |
| Filing Date | July 2, 2003 |
| First Named Inventor | Bhattacharyya, Arup |
| Group Art Unit | 2811 |
| Examiner Name | Unknown |

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Attorney Docket No: 1303.111US1

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| Examiner Name | Unknown |

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JMK RAN BROWN

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| | First Named Inventor | Bhattacharyya, Arup |
| | Group Art Unit | 2826 |
| | Examiner Name | Erdem, Fazli |
| Sheet 1 of 1 | Attorney Docket No: 1303.111US1 | |

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